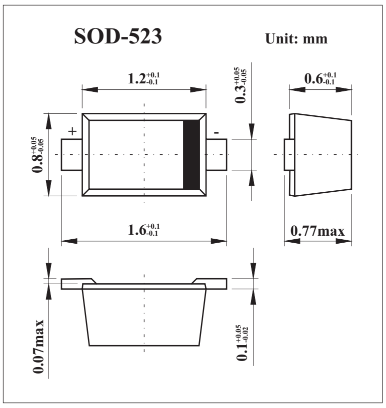
# Silicon Schottky Barrier Diode

# HSC226



## ■ Features

- ● Low reverse current, Low capacitance.
- ● Ultra small Flat Package (UFP) is suitable for surface mount design.

## ■ Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Repetitive peak reverse voltage | $V_{RRM}$ | 25 | V |
| Non-Repetitive peak forward surge current | $I_{FSM}$* | 200 | mA |
| Forward current | $I_F$ | 50 | mA |
| Junction temperature | $T_j$ | 125 | ℃ |
| Storage temperature | $T_{stg}$ | -55 to +125 | ℃ |

Note

10ms Sinewave 1pulse

## ■ Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Forward voltage | $V_F$ | $I_F$ = 1 mA | | | 0.33 | V |
| | | $I_F$ = 5 mA | | | 0.38 | |
| Reverse current | $I_R$ | $V_R$ = 20 V | | | 0.45 | μ A |
| Capacitance | C | $V_R$ =1 V, f = 1 MHz | | | 2.80 | pF |

## ■ Marking

| Marking | S4 |
|---|---|